To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSD276A

Silicon Schottky Barrier Diode for Detector

ADE-208-1385 (Z)

Rev.0
Jul. 2001

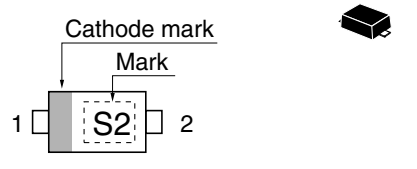
Features

- High forward current, Low capacitance.
- Super small Flat Package (SFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSD276A	S2	SFP

Pin Arrangement



1. Cathode
2. Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_O	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	I_R = 1 mA
Reverse current	I_R	—	—	50	μA	V_R = 0.5V
Forward current	I_F	35	—	—	mA	V_F = 0.5 V
Capacitance	C	—	—	0.85	pF	V_R = 0.5 V, f = 1 MHz
ESD-Capability *[1]	—	30	—	—	V	C = 200 pF, R = 0 Ω , Both forward and reverse direction 1 pulse.

Notes: 1. Failure criterion ; I_R > 100 μA at V_R = 0.5 V
2. Please do not use the soldering iron due to avoid high stress to the SFP package.

Main Characteristic

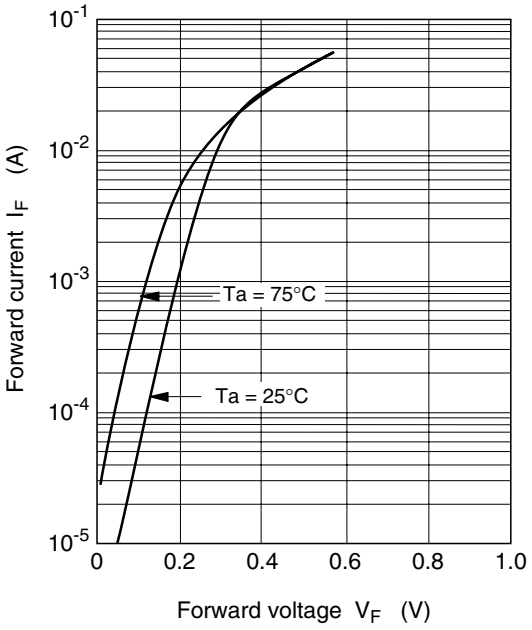


Fig.1 Forward current vs. Forward voltage

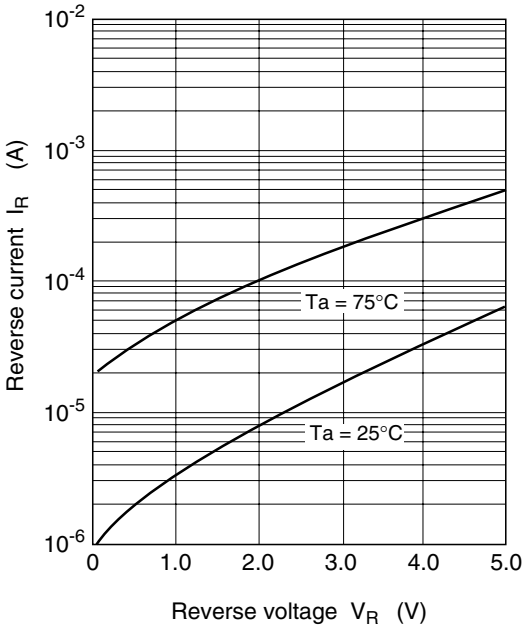


Fig.2 Reverse current vs. Reverse voltage

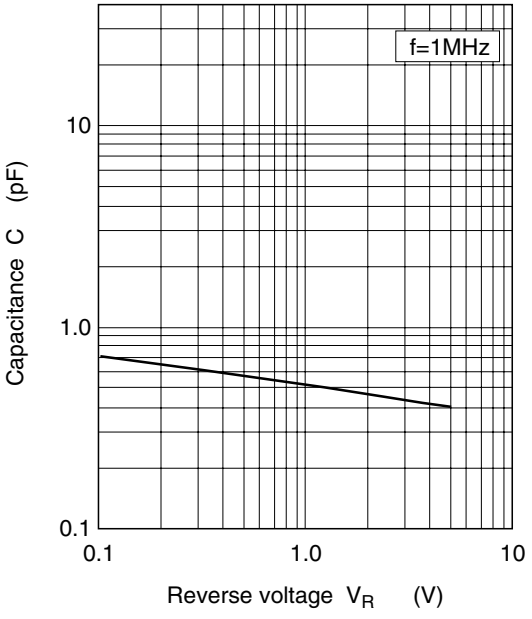
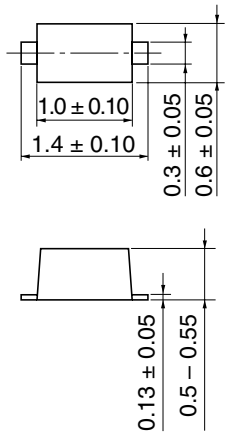


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	SFP
JEDEC	—
EIAJ	—
Mass (reference value)	0.0010 g

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